



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT

In re application of:

Calvez et al.

Group Art Unit: Unknown

Serial No. 10/550,843

Examiner: N/A

Filed: March 24, 2004 (I.A.)

For: IMPROVEMENTS IN AND
RELATING TO VERTICAL-
CAVITY SEMICONDUCTOR
OPTICAL DEVICES

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Alicia Curran

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicant wishes to call to the attention of the Examiner the documents cited on the accompanying Form PTO-1449. No concession is made that these documents are prior art, and applicant expressly reserves the right to antedate the documents as may be appropriate. Applicant requests that each of these documents be made of record in the above-identified application.

Respectfully submitted,


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Form PTO-1449

APR 20 2007

Docket No.: D-3214

Application No.: 10/550,843

**INFORMATION DISCLOSURE CITATION
IN AN APPLICATION**
(Use several sheets if necessary)

Applicant: Calvez et al.

Filing Date: March 24, 2004

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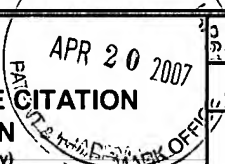
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AD	W.W. Bewley et al, "Thermal Characterization of Diamond-Pressure-Bond Heat Sinking for Optically Pumped Mid-Infrared Lasers", <i>IEEE Journal of Quantum Electronics</i> , Vol. 35, No. 11, 1999, p. 1597-1601.
AE	E. Staffan Björin, "High Gain, High Efficiency Vertical-Cavity Semiconductor Optical Amplifiers", <i>IPRM</i> , 2002, p. 307-310.
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BV	Coherent Laser Division. Sapphire Optically Pumped Semiconductor Lasers, Copyright 2002, Coherent, Inc.
BW	Coherent® Product Information. Sapphire 488 & 460 LP, Copyright 2006, Coherent, Inc.

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